PROCESS CPD91

Switching Diode

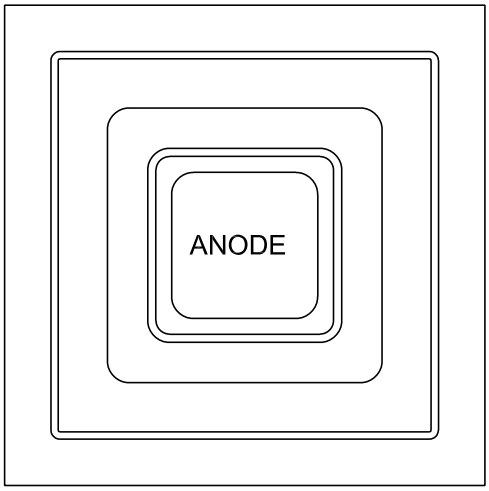
Low Leakage Switching Diode Chip

Central™ Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	11 x 11 MILS
Die Thickness	9.1 MILS
Anode Bonding pad Area	3.4 x 3.4 MILS
Top Side Metalization	Al - 15,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE: CATHODE R0

GROSS DIE PER 4 INCH WAFER

94,130

PRINCIPAL DEVICE TYPES

CMPD6001 Series
CMOD6001
CMLD6001
CMLD6001DO
CMDD6001

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R0 (20- January 2006)